



SANYO Semiconductors

DATA SHEET

2SJ670

P-Channel Silicon MOSFET

General-Purpose Switching Device

Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-100	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		-1.5	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-6	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (600mm²×0.8mm)	1.5	W
		Tc=25°C	3.5	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR) _{DSS}	I _D =-1mA, V _{GS} =0V	-100			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-100V, V _{GS} =0V			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-0.8A	1.3	2.3		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-0.8A, V _{GS} =-10V		410	535	mΩ
	R _{DS(on)2}	I _D =-0.8A, V _{GS} =-4V		530	745	mΩ
Input Capacitance	C _{iss}	V _{DS} =-20V, f=1MHz		535		pF
Output Capacitance	C _{oss}	V _{DS} =-20V, f=1MHz		43		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =-20V, f=1MHz		31		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		9		ns
Rise Time	t _r	See specified Test Circuit.		4.5		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		62		ns
Fall Time	t _f	See specified Test Circuit.		34		ns

Marking : NA

Continued on next page.

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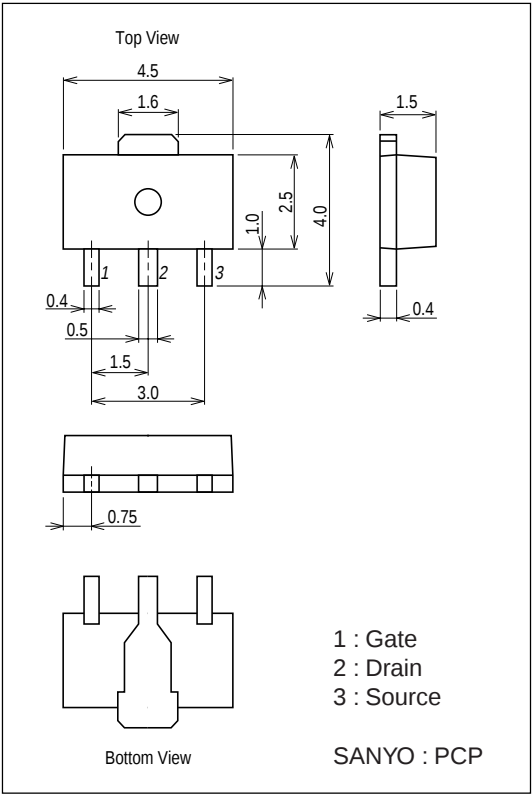
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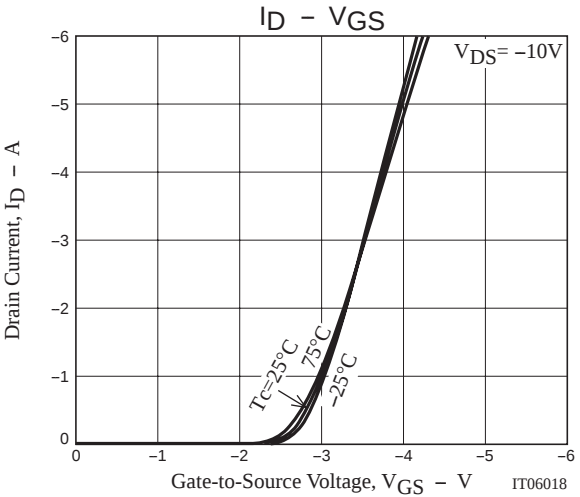
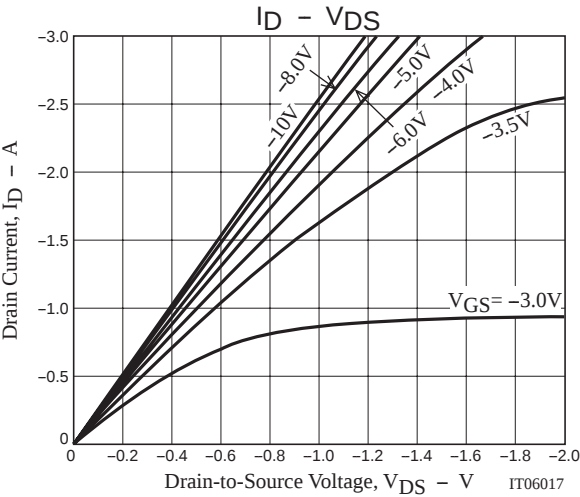
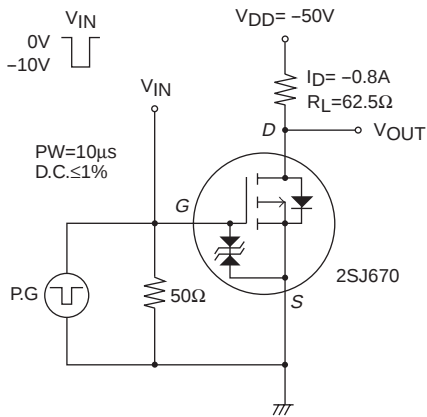
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V _{DS} =-50V, V _{GS} =-10V, I _D =-1.5A		11		nC
Gate-to-Source Charge	Qgs	V _{DS} =-50V, V _{GS} =-10V, I _D =-1.5A		2.6		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =-50V, V _{GS} =-10V, I _D =-1.5A		2		nC
Diode Forward Voltage	V _{SD}	I _S =-1.5A, V _{GS} =0V		-0.83	-1.2	V

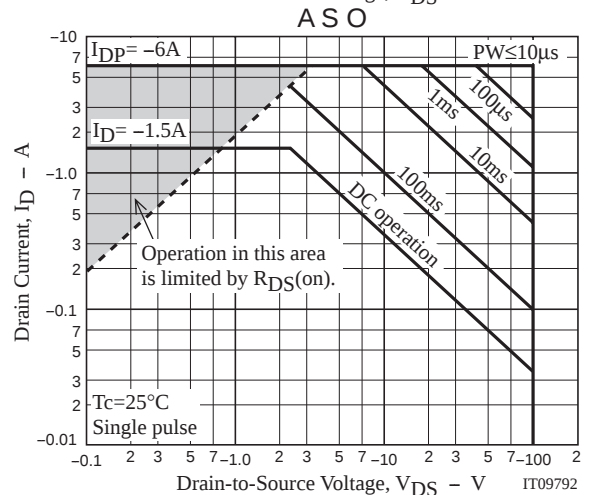
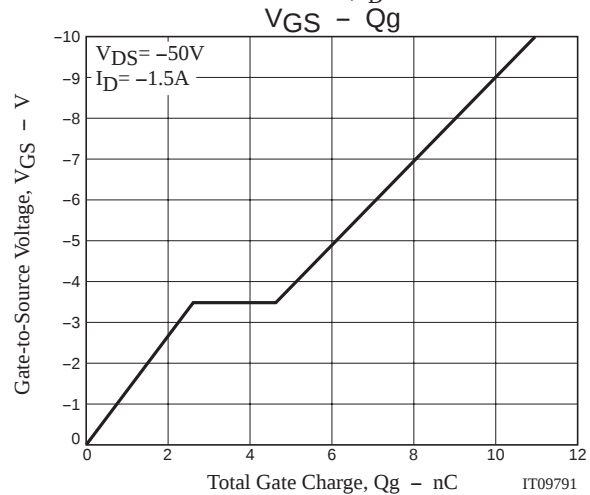
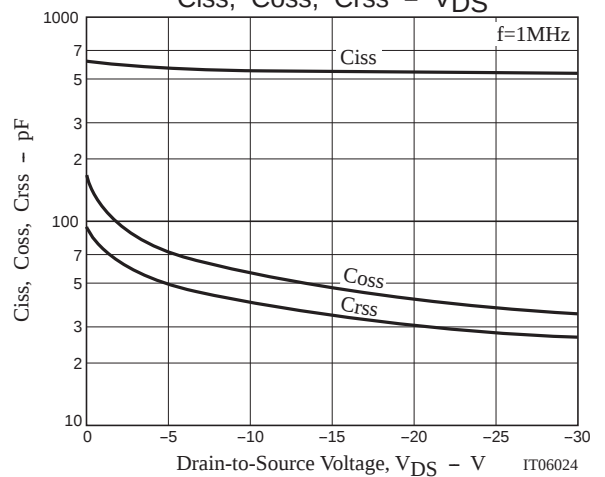
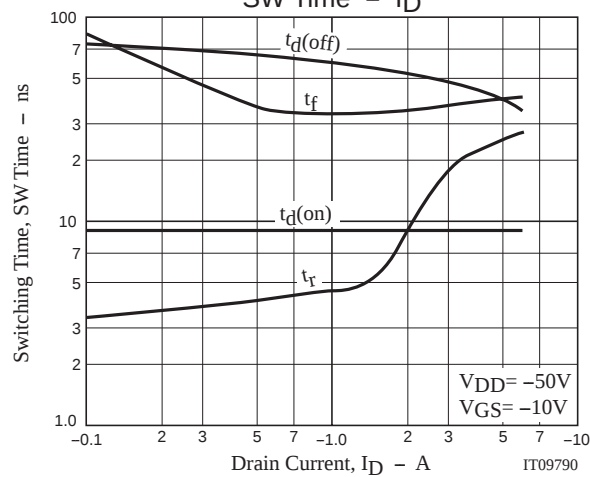
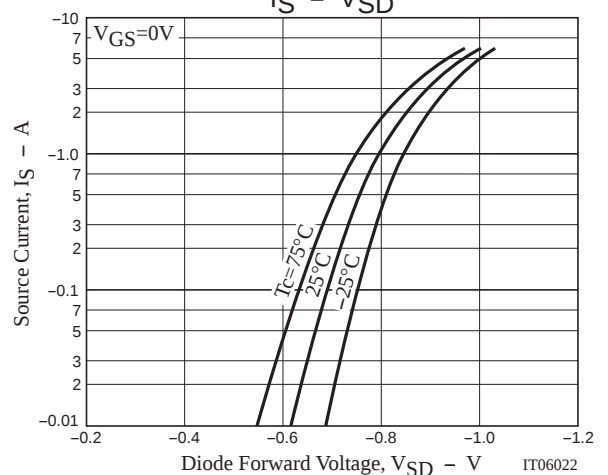
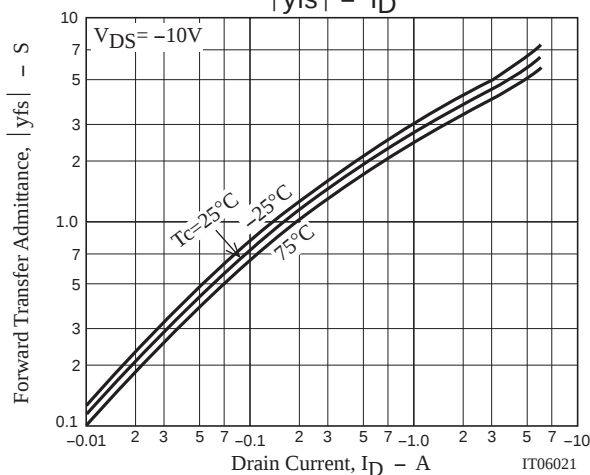
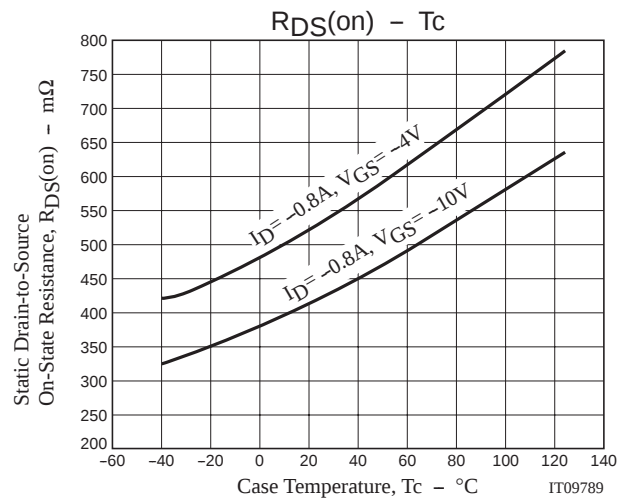
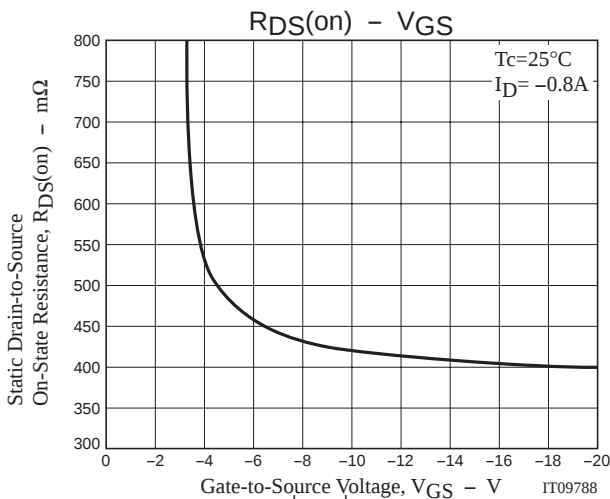
Package Dimensions

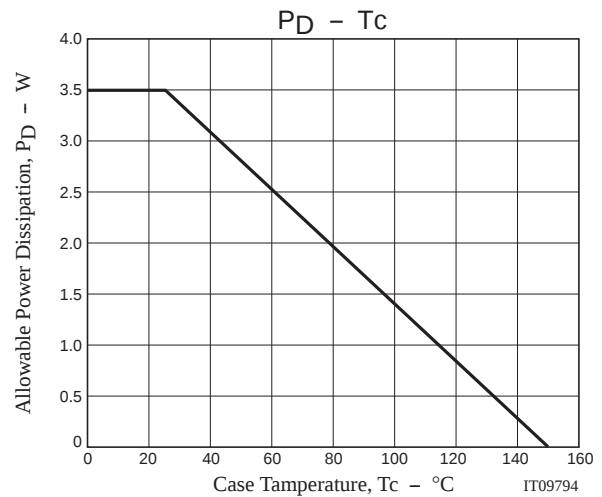
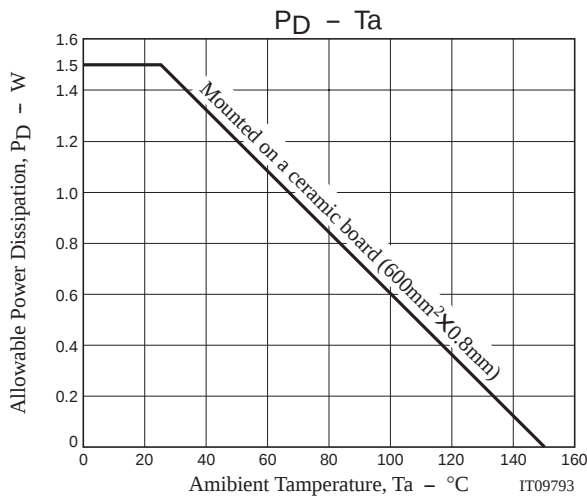
unit : mm (typ)
7007A-003



Switching Time Test Circuit







Note on usage : Since the 2SJ670 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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